REMARKS/ARGUMENTS

Claim 1 has been amended with the limitations of claim 3 as requested by the examiner; claim 3

has been canceled. Claims 2 and 4-35 are now dependent upon an acceptable base claim.

Claims 36 - 73 are previously allowed.

Claims Rejections-35 USC 103(a)

Applicants respectfully disagree with the use of Ramdani, 2003/0027409, as a meaningful

reference. Please note that Ramdani teaches the growth of single crystal germanium over a

single crystal metal oxide layer. Ramdani also teaches a discrete germanium transistor device

being connected to a discrete silicon device. Ramdani neither teaches nor suggests the growth of

a germanium layer in contact with a silicon layer, thereby forming a heterojunction; neither does

he teach nor suggest the operating of a heterojunction through a plurality of contacts to a

germanium layer and a silicon layer in contact with each other. Also please note that element

124 in Figure 30 is "... buffer layer 124 typically is a monocrystalline metal oxide or nitride

layer..." ¶[0102], 4th sentence.

Applicant respectfully requests that a timely Notice of Allowance be issued in this case.

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Respectfully submitted,

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